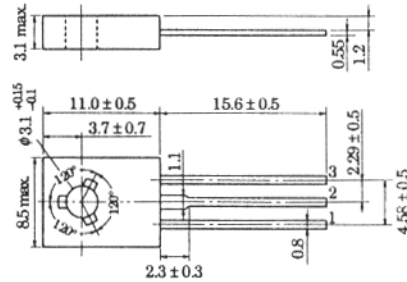


2SA715

SILICON PNP EPITAXIAL

LOW FREQUENCY POWER AMPLIFIER
COMPLEMENTARY PAIR WITH 2SC1162



1. Emitter
2. Collector
3. Base
(Dimensions in mm)

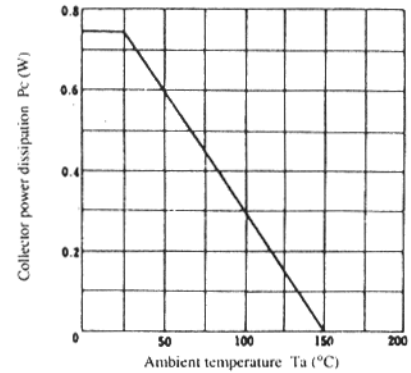
(JEDEC TO-126 MOD.)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SA715	Unit
Collector to base voltage	VCBO	-35	V
Collector to emitter voltage	VCEO	-35	V
Emitter to base voltage	VEBO	-5	V
Collector current	IC	-2.5	A
Collector peak current	iC(peak)	-3	A
Collector power dissipation	PC	0.75	W
	PC*	10	W
Junction temperature	Tj	150	°C
Storage temperature	Tsig	-55 to +150	°C

* Value at Tc = 25°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V(BR)CBO	IC = -1mA, IE = 0	-35	—	—	V
Collector to emitter breakdown voltage	V(BR)CEO	IC = -10mA, RBE = ∞	-35	—	—	V
Emitter to base breakdown voltage	V(BR)EBO	IE = -1mA, IC = 0	-5	—	—	V
Collector cutoff current	ICBO	VCB = -35V, IE = 0	—	—	-20	μA
DC current transfer ratio	hFE*	VCE = -2V, IC = -0.5A	60	—	320	
	hFE	VCE = -2V, IC = -1.5A (Pulse Test)	20	—	—	
Base to emitter voltage	VBE	VCE = -2V, IC = -1.5A (Pulse Test)	—	-1.0	-1.5	V
Collector to emitter saturation voltage	VCE(sat)	IC = -2A, IB = -0.2A (Pulse Test)	—	-0.5	-1.0	V
Gain bandwidth product	fT	VCE = -2V, IC = -0.2A (Pulse Test)	—	160	—	MHz

* The 2SA715 is grouped by hFE as follows.

B	C	D
60 to 120	100 to 200	160 to 320

2SA715

